

Emanuele Ucelli

List of Publications by Year in descending order

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Version: 2024-02-01

19
papers

1,220
citations

566801

15
h-index

839053

18
g-index

19
all docs

19
docs citations

19
times ranked

1666
citing authors

#	ARTICLE	IF	CITATIONS
1	Tuning the response of non-allowed Raman modes in GaAs nanowires. Journal Physics D: Applied Physics, 2016, 49, 095103.	1.3	7
2	Vertical InAs-Si Gate-All-Around Tunnel FETs Integrated on Si Using Selective Epitaxy in Nanotube Templates. IEEE Journal of the Electron Devices Society, 2015, 3, 176-183.	1.2	104
3	Three-Dimensional Magneto-Photoluminescence as a Probe of the Electronic Properties of Crystal-Phase Quantum Disks in GaAs Nanowires. Nano Letters, 2013, 13, 5303-5310.	4.5	28
4	Suppression of three dimensional twinning for a 100% yield of vertical GaAs nanowires on silicon. Nanoscale, 2012, 4, 1486.	2.8	73
5	Mobility and carrier density in p-type GaAs nanowires measured by transmission Raman spectroscopy. Nanoscale, 2012, 4, 1789.	2.8	60
6	Pressure Tuning of the Optical Properties of GaAs Nanowires. ACS Nano, 2012, 6, 3284-3291.	7.3	43
7	Three-Dimensional Multiple-Order Twinning of Self-Catalyzed GaAs Nanowires on Si Substrates. Nano Letters, 2011, 11, 3827-3832.	4.5	123
8	In(Ga)As quantum dot formation on group-III assisted catalyst-free InGaAs nanowires. Nanotechnology, 2011, 22, 195601.	1.3	48
9	Untangling the Electronic Band Structure of Wurtzite GaAs Nanowires by Resonant Raman Spectroscopy. ACS Nano, 2011, 5, 7585-7592.	7.3	126
10	Direct correlation of crystal structure and optical properties in wurtzite/zinc-blende GaAs nanowire heterostructures. Physical Review B, 2011, 83, .	1.1	193
11	Supercooling of nanoscale Ga drops with controlled impurity levels. Physical Review B, 2011, 84, .	1.1	13
12	Thermal conductivity of GaAs nanowires studied by micro-Raman spectroscopy combined with laser heating. Applied Physics Letters, 2010, 97, .	1.5	96
13	Optical Properties of InAs Quantum Dot Array Ensembles with Predetermined Lateral Sizes from 20 to 40 nm. Japanese Journal of Applied Physics, 2010, 49, 045201.	0.8	4
14	Compensation mechanism in silicon-doped gallium arsenide nanowires. Applied Physics Letters, 2010, 97, .	1.5	43
15	InAs Quantum Dot Arrays Decorating the Facets of GaAs Nanowires. ACS Nano, 2010, 4, 5985-5993.	7.3	99
16	P-Doping Mechanisms in Catalyst-Free Gallium Arsenide Nanowires. Nano Letters, 2010, 10, 1734-1740.	4.5	110
17	Investigation of a contacting scheme for self-assembled cleaved edge overgrown InAs nanowires and quantum dot arrays. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1620-1625.	0.8	0
18	Controlled synthesis of InAs wires, dot and twin-dot array configurations by cleaved edge overgrowth. Nanotechnology, 2008, 19, 045303.	1.3	15

#	ARTICLE	IF	CITATIONS
19	Long-range ordered self-assembled InAs quantum dots epitaxially grown on (110) GaAs. Applied Physics Letters, 2004, 85, 4750-4752.	1.5	35